

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	soi same (deplete or depleted or depleting or depletion) same dummy same gate same (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) with ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27
L2	1	soi and (deplete or depleted or depleting or depletion) same dummy same gate same (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) with ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:26
L3	74	soi and (deplete or depleted or depleting or depletion) and dummy same gate same (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) with ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27
L4	1	soi same (deplete or depleted or depleting or depletion) same dummy same gate same (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27
L5	121	soi and (deplete or depleted or depleting or depletion) and dummy same gate same (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) and ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27
L6	198	soi and (deplete or depleted or depleting or depletion) and dummy same gate and (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) and ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27
L7	260	soi and (deplete or depleted or depleting or depletion) and dummy and gate and (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) and ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27
L8	141	soi and (deplete or depleted or depleting or depletion) and (dummy near gate) and (implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) and ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:27

EAST Search History

L9	137	soi and (deplete or depleted or depleting or depletion) and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:28
L10	120	soi and (deplete or depleted or depleting or depletion) and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:28
L11	120	soi and (deplete or depleted or depleting or depletion) and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:28
L12	101	soi and (deplete or depleted or depleting or depletion) and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:29
L13	37	((soi or (silicon near2 insulator)) with (deplete or depleted or depleting or depletion)) and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:30

EAST Search History

L14	15	((soi or (silicon near2 insulator)) with (deplete or depleted or depleting or depletion)) and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode) and (sacrificial)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:31
L15	6	((soi or (silicon near2 insulator)) with (deplete or depleted or depleting or depletion)).ti,ab,clm. and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode) and (sacrificial)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:31
L16	6	((soi or (silicon near2 insulator)) same (deplete or depleted or depleting or depletion)).ti,ab,clm. and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode) and (sacrificial)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:32
L17	6	((soi or (silicon near2 insulator)) same (deplete or depleted or depleting or depletion)).ti,ab,clm. and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode) and (sacrificial) and (method or process)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:33

EAST Search History

L18	3	((soi or (silicon near2 insulator)) same (deplete or depleted or depleting or depletion)).ti,ab,clm. and (dummy near gate) and ((implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) near5 ion) and channel and (gate adj (dielectric or insulating or insulator or insulation or oxide)) and (gate near electrode) and (sacrificial) and (method or process).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 16:33
-----	---	---	---	----	----	------------------